

REPLACEMENT CLAIMS

1. (amended) A method of forming at least one contact in a magnetic random access memory cell structure, said method comprising:

forming a plurality of first conductive layers over an insulating layer formed over a substrate;

forming a plurality of first magnetic layers over said first conductive layers;

forming a plurality of second magnetic layers over said first magnetic layers, each of said plurality of second magnetic layers comprising a top conductive layer;

forming an insulating material in between each said plurality of first magnetic layers, in between each said plurality of second magnetic layers and over both said first and second magnetic layers; and

removing portion of said insulating material to expose at least one upper surface of said conductive layer.

21. (amended) A method of forming a plurality of self-aligned contacts in respective magnetic random access memory cell structures, said method comprising:

forming a plurality of first conductive layers over an insulating layer formed over a substrate;

forming a plurality of first magnetic layers over said first conductive layers;

forming a plurality of second magnetic layers over said first magnetic layers said plurality of second magnetic layers including respective top conductive layers;

forming an insulating material over said substrate, over both said plurality of first and second magnetic layers including said top conductive layers, and in between each said plurality of first magnetic layers and each said plurality of second magnetic layers;

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uncl*

removing portions of said insulating material from said top conductive layers to expose a plurality of upper surfaces of said top conductive layers associated with said second magnetic layers; and

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forming a plurality of second conductive layers over respective self-aligned contacts, said second conductive layers running substantially orthogonal to said first magnetic layers, one of said first and second conductive layers being bit lines and the other of said first and second conductive layers being word lines.